

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in this application--including presently cancelled claims 66, 68, 69, amended claim 67, and added new claims 82-85.

Listing of Claims:

Claims 1-24 (allowed).

Claims 25-65 (withdrawn).

Claim 66 (currently cancelled).

Claim 67 (currently amended): A thyristor semiconductor memory device comprising:

a thyristor comprising anode-emitter and cathode-emitter regions and two separate base regions of opposite type conductivity between the anode-emitter region and the cathode-emitter region;

an electrode capacitively-coupled to one of the two base regions; and

a shunt to shunt low-level current of at least one of the base regions, comprising:

a transistor having source and drain regions;

one of the source and drain regions electrically coupled to one of the cathode and anode regions of the thyristor;

the other of the source and drain regions being electrically coupled to one of the two base regions; and

the transistor further comprising a gate electrically coupled to the other of the two base regions and operable under bias to control a conductivity between the source and drain regions.

Claims 68-69 (currently cancelled).

Claims 70-81 (withdrawn).

Claim 82 (new): The semiconductor device of claim 2, in which the carbon within the at least one base-emitter junction causes a reduction in a bipolar gain of the thyristor.

Claim 83 (new): The semiconductor device of claim 82, in which current flows across the at least one base-emitter junction and the reduction in gain is greater at lower current levels than at higher current levels.

Claim 84 (new): The semiconductor device of claim 67, in which:

the transistor comprises a MOSFET;

the source/drain region of the MOSFET electrically coupled to the cathode region of the thyristor;

the drain/source region of the MOSFET electrically coupled to the p-base region of the thyristor; and

the gate of the MOSFET electrically coupled to the n-base region of the thyristor.

Claim 85 (new): The semiconductor device of claim 67, in which:

the transistor comprises a MOSFET defined in part by the source region, the drain region and the gate;

the drain/source region of the MOSFET electrically coupled to the anode region of the thyristor;

the source/drain region of the MOSFET electrically coupled to the n-base region of the thyristor; and

the gate of the MOSFET electrically coupled to p-base region of the thyristor.